## High Voltage 6-CH LED Driver Controller

### **General Description**

The RT8488 is a 6-CH LED driver controller that delivers well matched LED current to each channel of LED string. With external current sources, the number of LEDs per string is only limited by the current source and the  $V_{IN}/V_{OUT}$  conditions. The current mode PWM boost type controller operates at a programmable switching frequency of up to 1MHz, with a wide  $V_{IN}$  range covering from 7V to 28V. The switch driver is designed to drive industrial grade high power MOSFETs.

The PWM loop selects and regulates the LED string with the highest voltage string to 0.7V, thus allowing voltage mismatches between the LED strings. The RT8488 automatically detects and excludes any open and/or broken strings during operation from the PWM loop to prevent  $V_{OUT}$  from over voltage.

The LED currents on all channels are simply programmed with a resistor on each channel. Three convenient dimming methods are provided : 1. Analog dimming is linearly controlled by an external voltage. 2. True digitally controlled PWM dimming can regulate the duty cycle of the LED current. 3. For noise free PWM dimming, use an on board output clamping amplifier as a low pass filter to convert PWM dimming signals into analog dimming signals.

Other protection features include programmable output over voltage protection, PWM switch current limit and thermal shutdown.

### **Marking Information**



RT8488GQW : Product Number YMDNN : Date Code

### Features

- Wide Operation Voltage Range : 7V to 28V
- Programmable Channel Current
- 3% Current Matching Accuracy between Channels
- Programmable Switching Frequency
- Easy Analog and Digital Dimming Control
- Programmable Soft-Start
- Automatic Open Channel Detection
- Programmable Output Over Voltage Protection
- Under Voltage Lockout and Thermal Shutdown
- 32-Lead WQFN Package

#### Applications

- Building and Street Lighting
- LED TV Backlight
- LED Monitor Backlight
- Industrial Display Backlight

# Ordering Information

<sup>–</sup>Package Type QW : WQFN-32L 5x5 (W-Type)

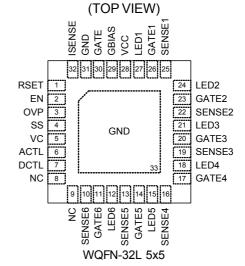
Lead Plating System G : Green (Halogen Free and Pb Free)

Note :

Richtek products are :

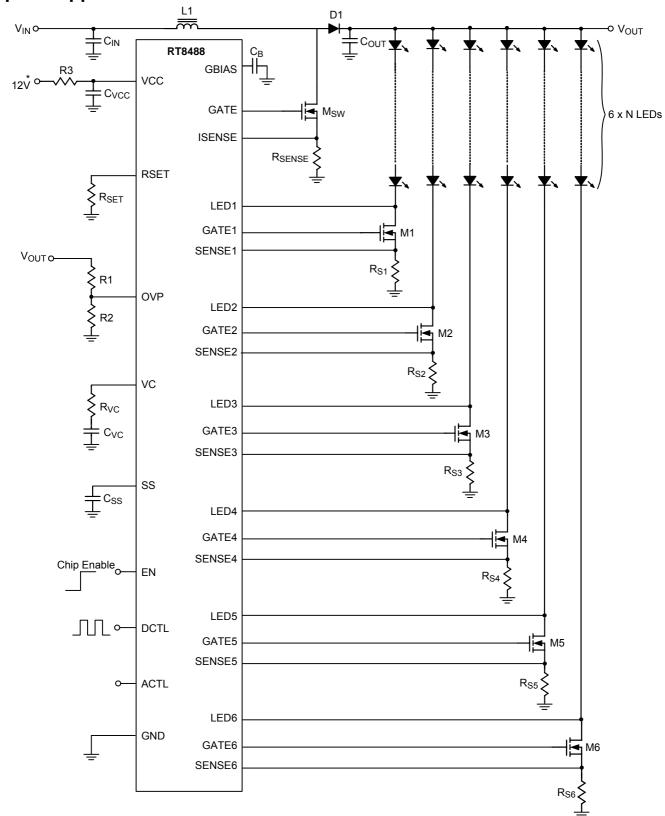
- RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

### **Pin Configurations**





## **Typical Application Circuit**



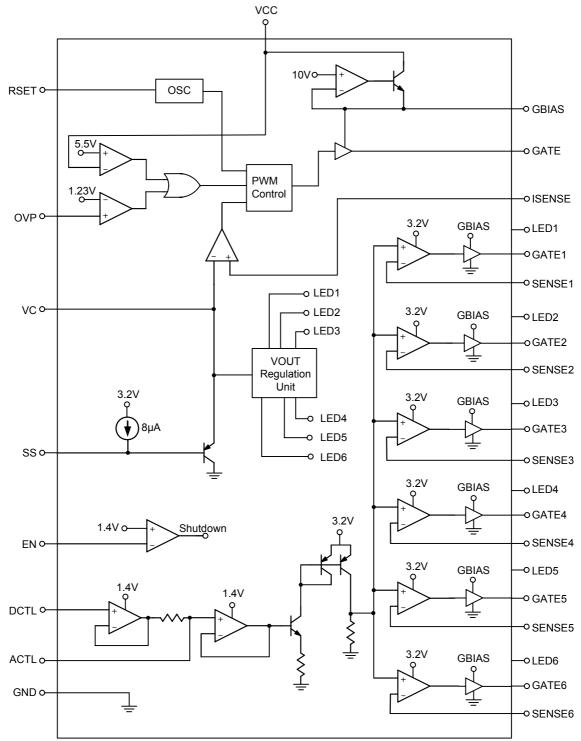
 $^{\star}$  : If V\_{IN} is operated above 12V, it is recommended to keep the V\_{CC} at 12V for optimal application

## **Functional Pin Description**

Pin No.	Pin Name	Pin Function			
1	RSET	Switching Frequency Set Pin. Put a resistor from RSET to GND to program to switching frequency. $f_{SW}$ = 310kHz when $R_{SET}$ = 40k $\Omega$ .			
2	EN	Chip Enable (Active High).			
3	OVP	Over Voltage Protection Pin. OVP pin threshold is around 1.23V. Use a resistor divider from Output to GND to program the OVP level.			
4	SS	Soft-Start Pin. Use a soft start cap from SS pin to GND to program the soft start time period. Around $5.5\mu$ A is sourcing out of SS pin.			
5	VC	Loop Compensation Pin.			
6	ACTL	Analog/PWM Dimming Control Pin. When used in analog dimming, ACTL control range is from 0.5V to 1.4V.			
7	DCTL	Digital PWM Dimming Control Pin. By adding a $0.1\mu$ F filter capacitor on the ACTL pin, the PWM dimming signal on the DCTL pin will be averaged out and converted into analog dimming signal on the ACTL pin.			
8, 9	NC	No Internal Connection.			
25, 22, 19 16, 13, 10	SENSEx	Source Pin of External MOSFETx (x = 1 to 6). The SENSEx pins are regulated around 225mV. Connect a sense resistor from this pin to GND. The LED current is programmed by $I_{LED} = 225mV / (sense resistance)$ when $V_{ACTL}$ is greater than 1.4V.			
26, 23, 20 17, 14, 11	GATEx	Gate Pin of External MOSFETx (x = 1 to 6). For LED drivers.			
27, 24, 21 18, 15, 12	LEDx	Drain Pin of External MOSFETx (x = 1 to 6). For LED drivers. Short the pin to GND if not used.			
28	VCC	Power Supply Pin. For good bypass, a low ESR capacitor is needed between this pin and GND.			
29	29 GBIAS Internal Gate Driver Bias Voltage (around 10V) Pin. Need a goo capacitor between this pin and GND.				
30	GATE	Gate Pin of External MOSFET. For the Boost PWM control loop.			
31, 33 (Exposed Pad)	GND	Ground Pin. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.			
32	ISENSE	Switch Current Sense Pin. Connect a sense resistor from this pin to GND. The switch current sense signal is used for boost current mode PWM loop control and power switch over current protection.			



### **Function Block Diagram**



### Absolute Maximum Ratings (Note 1)

• VCC	32V
• ISENSE	
DC	2V
< 200ns	6V
• GBIAS	14V
SENSE1 to SENSE6	
DC	1V
< 200ns	6V
• LED1 - LED6 (Note 5)	20V
• DCTL, ACTL, EN, OVP	10V
<ul> <li>Power Dissipation, P<sub>D</sub>@T<sub>A</sub> = 25°C</li> </ul>	
WQFN-32L 5x5	2.778W
<ul> <li>Package Thermal Resistance (Note 2)</li> </ul>	
WQFN-32L 5x5, $\theta_{JA}$	36°C/W
WQFN-32L 5x5, $\theta_{JC}$	6°C/W
Junction Temperature	150°C
Storage Temperature Range	–65°C to 150°C
Lead Temperature (Soldering, 10 sec.)	260°C
ESD Susceptibility (Note 3)	
HBM (Human Body Mode)	2kV
MM (Machine Mode)	200V

### Recommended Operating Conditions (Note 4)

Supply Voltage, V <sub>CC</sub>	7V to 28V
Junction Temperature Range	–40°C to 125°C

### **Electrical Characteristics**

(V\_{CC} = 12V, No Load, T\_A = 25°C, unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Тур	Max	Unit
Overall							
Supply Current		I <sub>VCC</sub>	$V_{VC} \le 0.4V$ (Switching off)		5	8	mA
Shutdown Current		I <sub>SHDN</sub>	$V_{EN} \leq 1.2V$		5		μA
EN Threshold Voltage	Logic-High	VIH		2			V
	Logic-Low	V <sub>IL</sub>				0.5	
EN Input Current		I <sub>EN</sub>	$V_{EN} \leq 3.3V$		2		μA
LED Current Programming							
SENSE1-SENSE6 Threshold			6V > V <sub>GATEx</sub> > 2V	214	225	236	mV
SENSE Voltage CH to CH Matching			$\frac{V_{(MAX)} - V_{(MIN)}}{2 \times V_{(avg)}}$		1.5	3	%
Analog Dimming ACTL Input Current		I <sub>ACTL</sub>	$V_{ACTL} \leq 6V$			10	μΑ
LED Current Off Threshold at ACTL		V <sub>ACTL_OFF</sub>			0.4		V

To be continued

## **RT8488**

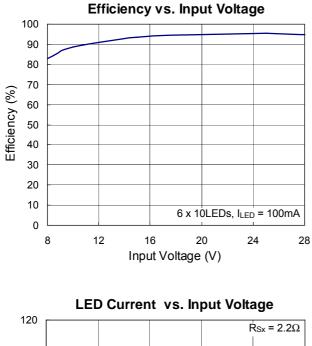


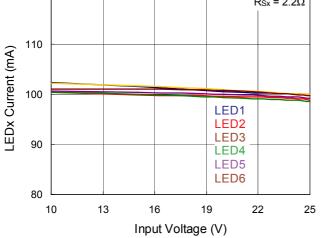
PWM Boost Converter         Switching Frequency         fsw         Rset = 40k0         220         280         34           Minimum Off-Time         RSET = 40k0          300          0.1          300          10.1          0.7          130          130          130          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          10.7          <	Unit	Max	Тур	Min	Test Conditions	Symbol	Parameter	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	V		1.4			V <sub>ACTL_ON</sub>		
PWM Boost Converter           Switching Frequency $f_{SW}$ $R_{SET} = 40k\Omega$ 220         280         34           Minimum Off-Time $R_{SET} = 40k\Omega$ 300          300          300          300          300          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.1          0.7          1.0 <t< td=""><td>μA</td><td>1</td><td></td><td></td><td><math>V_{DCTL} \leq 6V</math></td><td>IDCTL</td><td></td></t<>	μA	1			$V_{DCTL} \leq 6V$	IDCTL		
$\begin{array}{c c c c c c c c c c c c c c c c c c c $							PWM Boost Converter	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	kHz	340	280	220	R <sub>SET</sub> = 40kΩ	f <sub>SW</sub>	Switching Frequency	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	ns		300				Minimum Off-Time	
Amplifier Output Current $I_{VC}$ $2.4V > V_{VC} > 0.2V$ $\pm 30$ VC Threshold for PWM Switch Off $0.7$ $0.7$ Switch Gate DriverIGBIAS VoltageVGBIASIGBIAS = 20mA10GATE High Voltage $V_{GATE_{-H}}$ $I_{GATE} = -20mA$ $7.7$ GATE Low Voltage $V_{GATE_{-L}}$ $I_{GATE} = -0.1mA$ $8.2$ GATE Drive Rise and Fall Time1nF load at Gate $0.7$ GATE 1 to 6 High Voltage $V_{GATE_{-L}}$ $I_{GATEx} = -2mA$ $8.1$ GATE 1 to 6 Low Voltage $V_{GATE_{-L}}$ $I_{GATEx} = -2mA$ $8.1$ GATE 1 to 6 Low Voltage $V_{GATEx_{-L}}$ $I_{GATEx} = 2mA$ $0.8$ GATE 1 to 6 Low Voltage $V_{GATEx_{-L}}$ $I_{GATEx} = 2mA$ $0.8$ OVP and Soft-StartOVP $1.23$ $0.7$ OVP Input Current $I_{OVP}$ $V_{OVP} \leq 1.23V$ $1$	V		0.1			V <sub>LED</sub>		
VC Threshold for PWM Switch Off         Image: Mark Switch Switch Switch Gate Driver         Image: Mark Switch Switch Gate Driver         Image: Switch	V		0.7		Highest Voltage LED String	$V_{LED}$	Regulated V <sub>LED</sub>	
Off        0.7          Switch Gate Driver       GBIAS Voltage $V_{GBIAS}$ $I_{GBIAS} = 20mA$ 10          GATE High Voltage $V_{GATE_{-}H}$ $I_{GATE} = -20mA$ 7.7          GATE Low Voltage $V_{GATE_{-}H}$ $I_{GATE} = -0.1mA$ 8.2          GATE Low Voltage $V_{GATE_{-}L}$ $I_{GATE} = 20mA$ 0.7          GATE Drive Rise and Fall Time       1nF load at Gate        0.4          GATE 1 to 6 High Voltage $V_{GATE_{-}H}$ $I_{GATEx} = -2mA$ 8.1          GATE1 to 6 Low Voltage $V_{GATE_{-}L}$ $I_{GATEx} = -0.1mA$ 0.8          GATE1 to 6 Low Voltage $V_{GATEx_{-}H}$ $I_{GATEx} = 2mA$ 0.8          GATE1 to 6 Low Voltage $V_{GATEx_{-}L$ $I_{GATEx} = 0.1mA$ 0.6          OVP and Soft-Start $0.2mA$ 0.6           OVP Input Current       IOVP       VOVP         1.23	μA		±30		2.4V > V <sub>VC</sub> > 0.2V	I <sub>VC</sub>	Amplifier Output Current	
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GATE1 to 6 Low Voltage $V_{GATEx_L}$ $I_{GATEx} = -0.1 \text{mA}$ 8.3 $QATE1$ to 6 Low Voltage $V_{GATEx_L}$ $I_{GATEx} = 2\text{mA}$ 0.8 $OVP$ and Soft-Start $I_{GATEx} = 0.1 \text{mA}$ 0.6 $OVP$ Threshold $V_{OVP}$ 1.23 $OVP$ Input Current $I_{OVP}$ $V_{OVP} \le 1.23V$ 1	- v		8.1		I <sub>GATEx</sub> = -2mA	V <sub>GATEx_H</sub>		
GATE1 to 6 Low Voltage       VGATEX_L       IGATEX = 0.1mA        0.6          OVP and Soft-Start       OVP Threshold       VOVP        1.23          OVP Input Current       IOVP       VOVP ≤ 1.23V        1	v		8.3		I <sub>GATEx</sub> = -0.1mA		GATET to 6 Fight voltage	
OVP and Soft-Start     VOVP      0.6        OVP Threshold     VOVP      1.23        OVP Input Current     IOVP     VOVP ≤ 1.23V      1	- v		0.8		I <sub>GATEx</sub> = 2mA	VGATEx_L		
OVP Threshold         VOVP          1.23            OVP Input Current         IOVP         VOVP $\leq$ 1.23V          1	v		0.6		I <sub>GATEx</sub> = 0.1mA		GATET to 6 LOW VOItage	
OVP Input CurrentIVV1							OVP and Soft-Start	
	V		1.23			Vovp	OVP Threshold	
	μA		1		$V_{OVP} \le 1.23V$	IOVP	OVP Input Current	
	μA		8		$V_{SS} \le 3.2V$	I <sub>SS</sub>	Soft-Start Pin Current	
Thermal Protection					•		Thermal Protection	
Thermal Shutdown temperature T <sub>SD</sub> 150	°C		150			T <sub>SD</sub>		
	°C		20			$\Delta T_{SD}$		

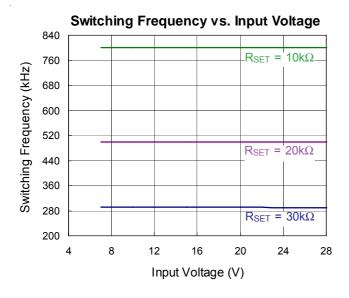
- **Note 1.** Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possiblity to affect device reliability.
- Note 2.  $\theta_{JA}$  is measured in natural convection at  $T_A = 25^{\circ}C$  on a high effective thermal conductivity four-layer test board of JEDEC 51-7 thermal measurement standard. The measurement case position of  $\theta_{JC}$  is on the exposed pad of the package.
- Note 3. Devices are ESD sensitive. Handling precaution is recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.
- Note 5. Adding a series resistor of at least  $20k\Omega$  for higher pin voltage.

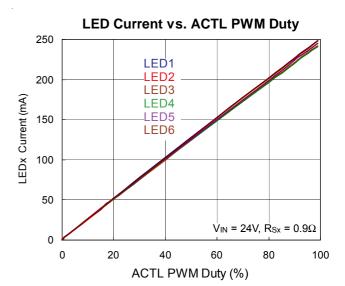


### **Typical Operating Characteristics**

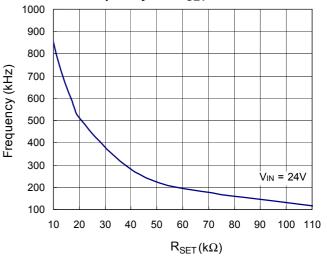


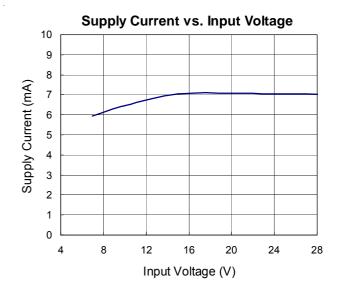




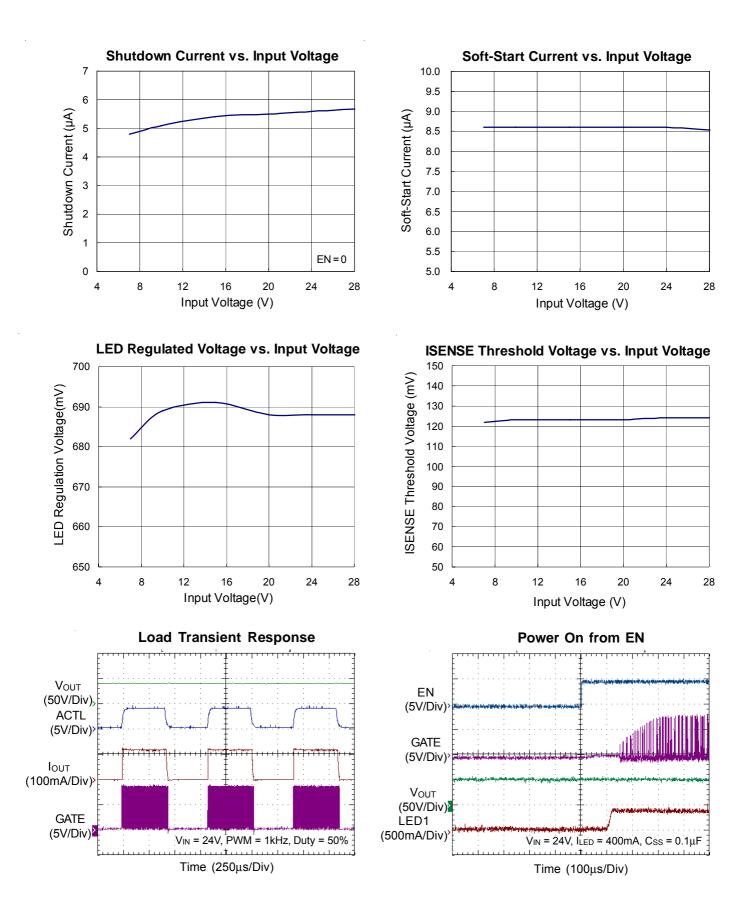


Frequency vs. R<sub>SET</sub> Resistance





8



### **Application Information**

The RT8488 is a 6-CH programmable current source controller for LED backlight or lighting application.

By detecting the minimum voltage required to drive each LED string and hence to set the boost output accordingly, this topology reduces power dissipation and increases overall efficiency of the LED lighting system.

The individual current source channel regulates the current flow to give accurate current sinking for each LED string.

The external N-MOSFET current source will accommodate the power dissipation difference among channels resulting from the forward voltage difference between the LED strings.

Both digital PWM dimming signal and analog voltage signal can be used to control the LED current of each channel.

With high speed current source N-MOSFET drivers, the RT8488 features highly accurate current matching of  $\pm 3$  percent, while also providing very fast turn-on and turn-off times. This allows a very narrow minimum on or off pulse, which increases dimming range and provides higher linearity.

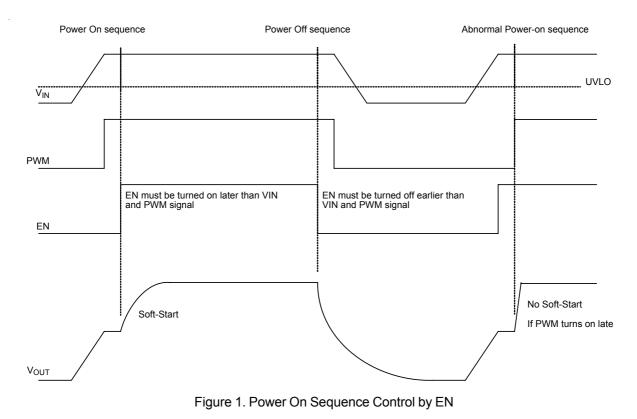
The RT8488 integrates adjustable switching frequency and soft-start, and provides the circuitry for over temperature, over voltage and current limit protection features.

#### Input UVLO

The input operating voltage range of the RT8488 is 7V to 28V. An input capacitor at the VCC pin can reduce ripple voltage. It is recommended to use a ceramic  $10\mu$ F or larger capacitance as the input capacitor. This IC provides an Under Voltage Lockout (UVLO) function to enhance the stability when start-up. The UVLO rising input voltage threshold is set at 5.5V typically with a 0.7V hysteresis.

#### **Power Sequence**

Refer to below Figure 1 and 2. The recommended power on sequence states that the PWM signal should be ready before EN and/or  $V_{IN}$  is ready. Otherwise, the soft-start function will be disabled. As for power off sequence, EN/  $V_{IN}$  must be pulled low within 10ms to prevent "hardstart" as shown as Figure 3.



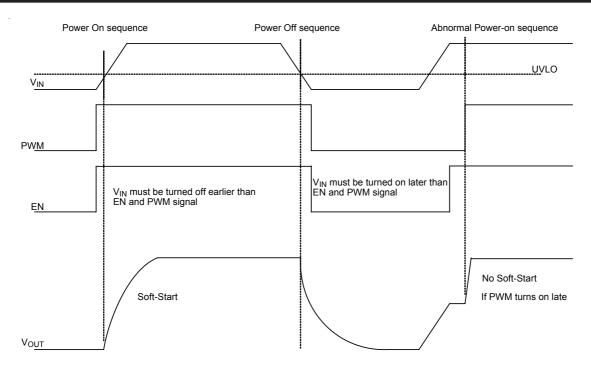


Figure 2. Power On Sequence Control by  $V_{\mbox{\scriptsize IN}}$ 

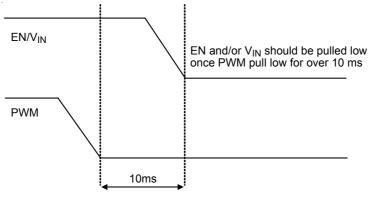


Figure 3. To Prevent "hard-start" Sequence

#### Soft-Start

The soft-start of the RT8488 can be achieved by connecting a capacitor from the SS pin to GND. The built in soft-start circuit reduces the start up current spike and output voltage overshoot. The soft-start time is determined by the external capacitor charged by an internal  $8\mu$ A constant charging current. The SS pin directly limits the rate of voltage rise on the VC pin, which in turn limits the peak switch current.

The soft-start interval is set by the soft-start capacitor selection according to the equation :

$$t_{SS} = C_{SS} \times \frac{3.2V}{8\mu A}$$
 (s)

A typical value for the soft-start capacitor is  $0.1\mu$ F. The soft-start pin reduces the oscillator frequency and the maximum current in the switch. The soft-start capacitor is discharged when EN/UVLO falls below its threshold, during an over-temperature event, or during a GBIAS under voltage event.

#### **GBIAS** Regulator Operation

The GBIAS pin requires a capacitor for stable operation and also to store the charge for the large GATE switching currents. Choose a 10V rated low ESR, X7R or X5R ceramic capacitor for best performance. The value of the capacitor is determined primarily by the stability of the regulator rather than the gate charge of the switching N-MOSFET. A 1 $\mu$ F capacitor will be adequate for most applications.

Place the capacitor close to the IC to minimize the trace length to the GBIAS pin and also to the IC ground. An internal current limit on the GBIAS protects the RT8488 from excessive on chip power dissipation.

If the input voltage,  $V_{IN}$ , does not exceed 10V, then the GBIAS pin should be connected to the input supply. Be aware that a typical 20mA current will load the GBIAS to shutdown.

#### **Loop Compensation**

The RT8488 uses an internal error amplifier, in which through its compensation pin (VC) the loop response is optimized for specific applications. The external inductor, output capacitor, compensation resistor, and compensation capacitor determine the loop stability. The inductor and output capacitor are chosen based on performance, size and cost. The compensation resistor and capacitor at VC are selected to optimize control loop response and stability.

The compensation resistor and capacitor are connected in series from the VC pin to GND to provide a pole and a zero for proper loop compensation. The typical compensation values for RT8488 is  $1.8k\Omega$  and 3.3nF.

#### **LED Current Setting**

The maximum current of channel 1 to 6 is programmed by placing an appropriate sense resistor at each LED string. When the voltage of ACTL is higher than 1.4V, the LED current can be calculated by the following equation :

$$I_{\text{LED, MAX}} = \frac{225\text{mV}}{\text{R}_{\text{Sx}}}$$
 (mA)

where,  $R_{\text{Sx}}$  is the resistor between external regulating N-MOSFET and GND.

The ACTL pin should be tied to a voltage higher than 1.4V to get the full scale 225mV (typical) threshold across the sense resistor. The ACTL pin can also be used to dim the

LED current to zero, although relative accuracy decreases with the decreasing voltage sense threshold. When the ACTL pin voltage is less than 1.4V, the LED current is :

$$I_{LED} = \frac{(V_{ACTL} - 0.4) \times 225mV}{R_{Sx}} \quad (mA)$$

The ACTL pin can also be used in conjunction with a thermistor to provide over temperature protection for the LED load, or with a resistive voltage divider to  $V_{IN}$  to reduce output power and switching current when  $V_{IN}$  is low.

#### **Brightness Control**

For LED applications where a wide dimming range is required, two methods are available: analog dimming and PWM dimming. The easiest method is to simply vary the DC current through the LED by analog dimming.

However, a better dimming method is PWM dimming, which switches the LED on and off via different duty cycle to control the average LED current. The PWM dimming offers several advantages over analog dimming and is more preferred by LED manufacturers. One advantage is the chromaticity of the LEDs which remains unchanged since the LED current is either zero or at the programmed current. Another advantage of PWM dimming over analog dimming is that a wider dimming range is possible.

The RT8488 features both analog and digital dimming control. Analog dimming is linearly controlled by an external voltage (0.4V to 1.4V) at the ACTL pin. A very high contrast ratio is true digital PWM dimming which can be achieved by driving the ACTL pin with a PWM signal at a recommended PWM frequency of 100Hz to 10kHz.

Dimming frequency can be sufficiently adjusted from 100Hz to 30kHz. However, LED current cannot be 100% proportional to the duty cycle, especially for high frequency and low duty ratio, because of physical limitation caused by internal switching frequency. Referring to Figure 4, the minimum dimming duty can be as low as 1% for the frequency range from 100Hz to 300Hz. For the dimming frequency from 300Hz to 1kHz, the minimum dimming duty is about 5%. If the frequency is increased from 1kHz to 30kHz, the minimum dimming duty will be about 10%.

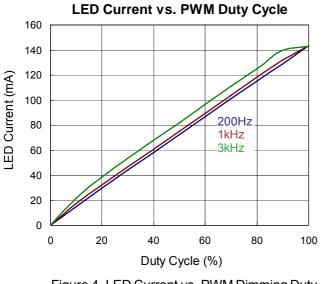


Figure 4. LED Current vs. PWM Dimming Duty Cycle

#### Programmable Switching Frequency

The RSET frequency adjust pin allows the user to program the switching frequency from 100kHz to 1MHz in order to optimize efficiency and performance or minimize external component size. Higher frequency operation yields smaller component size but increases switching losses and gate driving current, and may not allow sufficiently high or low duty cycle operation. Lower frequency operation gives better performance, but is more costly with larger external component size. An external resistor from the RSET pin to GND is required do not leave this pin open. For an appropriate  $R_{SET}$  value, refer to Figure 5.

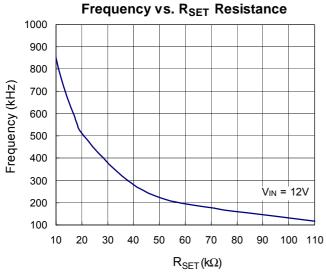


Figure 5. Switching Frequence vs  $R_{\text{SET}}$ 

#### LED Pin External Resistor Connection

The RT8488 equips 6 channel LED drivers and each channel supports numerous LEDs. The 6 LED strings are connected from  $V_{OUT}$  to pin LEDx (x = 1 to 6) respectively. If one of the LED channel is not used, the LEDx (x = 1 to 6) pins should be connected to ground directly.

In this case, there should be a current limiting resistor between external MOSFET drain node and LEDx pin to limit the LEDx pin input current below  $100\mu$ A.

The formula for this resistor is

 $Rx = (V_{OUT} - |V_{LEDx(MAX)}|) / 100\mu A$ 

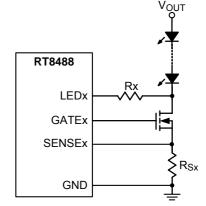


Figure 6. LED Pin External Resistor Connection

#### **Input Over Current Protection**

The resistor, R<sub>SENSE</sub>, between the source of the external switching N-MOSFET and GND should be selected to provide adequate switch current.

The RT8488 senses the inductor current through ISENSE pin in the switch on period. The duty cycle depends on the current sense signal summed with the internal slope compensation and compared to the VC signal. The external N-MOSFET will be turned off when the current signal is larger than the VC signal. In the off period, the inductor current will descend. The external N-MOSFET is turned on by the oscillator in the next beginning cycle. To drive the application without exceeding the 120mV (typical) current limit threshold on the ISENSE pin of the RT8488. Select a resistor that gives a switch current of at least 20% greater than the required LED current according to :

$$\mathsf{R}_{\mathsf{SENSE}} = \left(\frac{\mathsf{V}_{\mathsf{IN}} \times 0.1\mathsf{V}}{\mathsf{V}_{\mathsf{OUT}} \times \mathsf{I}_{\mathsf{OUT}}}\right) \quad (\Omega)$$

The ISENSE pin input to RT8488 should be a kelvin connection to the positive terminal of  $R_{\text{SENSE}}$ .

#### **Output Over Voltage Protection Setting**

The RT8488 is equipped with Over Voltage Protection (OVP) function. When the voltage at the OVP pin exceeds a threshold of approximately 1.23V, the power switch is turned off. The power switch can be turned on once again after the voltage at the OVP pin drops below 1.23V. The output voltage can be clamped at a certain voltage level set by the following equation :

 $V_{OUT,OVP} = 1.23 \times \left(1 + \frac{R1}{R2}\right)$ 

where R1 and R2 make up the resistive voltage divider from  $V_{OUT}$  to GND with the divider center node connected to the OVP pin.

As long as one string is in normal operation, the controller will automatically ignore the open strings and continue to regulate the current for the string(s) in normal operation.

#### **Over Temperature Protection**

The RT8488 has an over temperature protection (OTP) function to prevent overheating caused by excessive power dissipation. The OTP function will shut down switching operation when the die junction temperature exceeds 150°C. The chip will automatically start to switch again once the die junction temperature starts cooling down by approximately 20°C.

#### **Inductor Selection**

The inductor for the RT8488 should have a saturation current rating appropriate to the maximum switch current. Choose an inductor value based on the operating frequency, input voltage and output voltage to provide a current mode ramp during the MOS switching. Allow the peak to peak inductor ripple to be  $\pm 30\%$  of the output current. The following equations are useful to estimate the inductor value :

 $L = \frac{(V_{OUT} - V_{IN}) \times (V_{IN})^{2}}{2 \times I_{OUT} \times f \times (V_{OUT})^{2} \times 0.3}$ 

The inductor must be selected with a saturation current rating greater than the peak current provided by the following equation :

$$I_{\text{PEAK}} = \frac{V_{\text{OUT}} \times I_{\text{OUT}}}{\eta \times V_{\text{IN}}} + \frac{V_{\text{IN}} \times T}{2 \times L} \times \left(\frac{V_{\text{OUT}} - V_{\text{IN}}}{V_{\text{OUT}}}\right)$$

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where

V<sub>OUT</sub> = maximum output voltage.

V<sub>IN</sub> = minimum input voltage.

f = operating frequency.

 $I_{OUT}$  = sum of current from all LED strings.

 $\boldsymbol{\eta}$  is the efficiency of the power converter.

The boost converter operates in discontinuous conduction mode over the entire input voltage range when the L1 inductor value is less than this value L. With an inductance greater than L, the converter operates in continuous conduction mode at the minimum input voltage and may be discontinuous at higher voltages.

#### **Power MOSFET Selection**

For applications operating at high input or output voltages, the power N-MOSFET switch is typically chosen for drain voltage  $V_{DS}$  rating and low gate charge. Consideration of switch on resistance,  $R_{DS(ON)}$ , is usually secondary because switching losses dominate power loss. The GBIAS regulator on the RT8488 has a fixed current limit to protect the IC from excessive power dissipation at high  $V_{IN}$ , so the N-MOSFET should be chosen such that the product of  $Q_G$  at 7V and the switching frequency does not exceed the GBIAS current limit.

#### Schottky Diode Selection

The Schottky diode, with their low forward voltage drop and fast switching speed, is necessary for the RT8488 applications. In addition, power dissipation, reverse voltage rating and pulsating peak current are important parameters of the Schottky diode that must be considered. Choose a suitable Schottky diode whose reverse voltage rating is greater than the maximum output voltage. The diode's average current rating must exceed the average output current. The diode conducts current only when the power switch is turned off (typically less than 50% duty cycle). If using the PWM feature for dimming, it is important to consider diode leakage, which increases with the temperature, from the output during the PWM low interval. Therefore, choose the Schottky diode with sufficiently low leakage current.

## **RT8488**

#### **Capacitor Selection**

The input capacitor reduces current spikes from the input supply and minimizes noise injection to the converter. For most applications, a  $10\mu$ F ceramic capacitor is sufficient. A value higher or lower may be used depending on the noise level from the input supply and the input current to the converter.

In boost applications, the output capacitor is typically a ceramic capacitor selected based on the output voltage ripple requirements. The minimum value of the output capacitor,  $C_{OUT}$ , is approximately given by the following equation :

$$C_{OUT} = \frac{I_{OUT} \times (V_{OUT} - V_{IN})}{\eta \times V_{RIPPLE} \times V_{OUT} \times f}$$

where  $V_{RIPPLE}$  is rhe output voltage ripple, for LED applications, the equivalent resistance of the LED is typically low and the output filter capacitor should be sized to attenuate the current ripple. Use of X7R type ceramic capacitors is recommended. Lower operating frequencies will require proportionately higher capacitor values.

#### **Thermal Considerations**

For continuous operation, do not exceed absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by the following formula :

$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = (\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}) / \theta_{\mathsf{J}\mathsf{A}}$$

where  $T_{J(MAX)}$  is the maximum junction temperature,  $T_A$  is the ambient temperature, and  $\theta_{JA}$  is the junction to ambient thermal resistance.

For recommended operating condition specifications of the RT8488, the maximum junction temperature is 125°C and T<sub>A</sub> is the ambient temperature. The junction to ambient thermal resistance,  $\theta_{JA}$ , is layout dependent. For WQFN-32L 5x5 packages, the thermal resistance,  $\theta_{JA}$ , is 36°C/W on a standard JEDEC 51-7 four-layer thermal test board. The maximum power dissipation at T<sub>A</sub> = 25°C can be calculated by the following formula :

 $P_{D(MAX)}$  = (125°C - 25°C) / (36°C/W) = 2.778W for WQFN-32L 5x5 package

The maximum power dissipation depends on the operating ambient temperature for fixed  $T_{J(MAX)}$  and thermal resistance,  $\theta_{JA}$ . For the RT8488 package, the derating curve in Figure 7 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

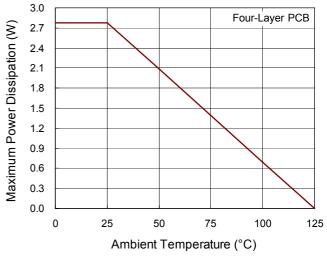


Figure 7. Derating Curves for RT8488 Package

#### Layout Consideration

PCB layout is very important when designing power switching converter circuits. Some recommended layout guidelines are suggested as follows :

- ➤ The power components L1, D1, C<sub>IN</sub>, M<sub>SW</sub> and C<sub>OUT</sub> must be placed as close to each other as possible to reduce the ac current loop area. The PCB trace between power components must be as short and wide as possible due to large current flow through these traces during operation.
- Place L1 and D1, which are connected to N-MOSFET, as close as possible. The trace should be as short and wide as possible.
- The input capacitor, C<sub>VCC</sub> must be placed as close to the VCC pin as possible.
- Place the compensation components to the VC pin as close as possible to avoid noise pick up.

## **RT8488**



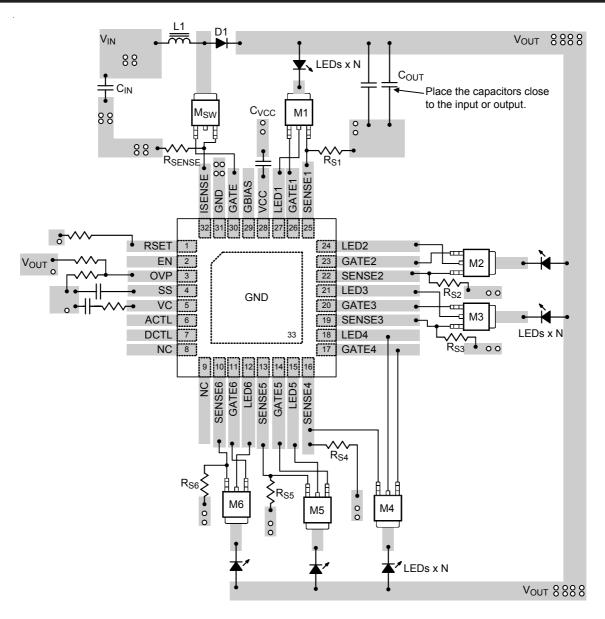
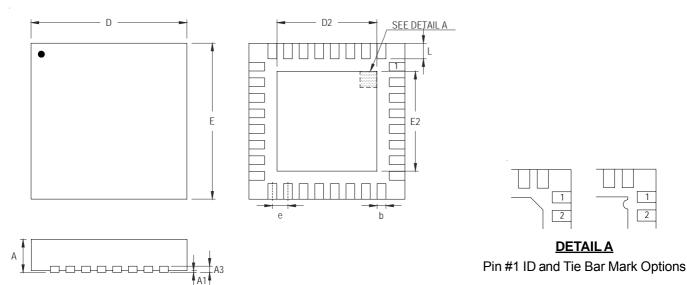


Figure 8. PCB Layout Guide

### **Outline Dimension**



Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions	n Millimeters	<b>Dimensions In Inches</b>		
	Min	Max	Min	Max	
А	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.175	0.250	0.007	0.010	
b	0.180	0.300	0.007	0.012	
D	4.950	5.050	0.195	0.199	
D2	3.400	3.750	0.134	0.148	
E	4.950	5.050	0.195	0.199	
E2	3.400	3.750	0.134	0.148	
е	0.500		0.0	20	
L	0.350	0.450	0.014	0.018	



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